

1200V, 15A, Trench FS II Fast IGBT

General Description

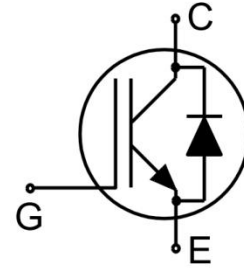
Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 1200V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

Features

- Trench FSII Technology offering
- Very low $V_{CE(sat)}$
- High speed switching
- Positive temperature coefficient in $V_{CE(sat)}$
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- Air Condition
- Inverters
- Motor drives



Schematic diagram

Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE15TD120BT	TO-247	NCE15TD120BT



TO-247

Absolute Maximum Ratings ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate- Emitter Voltage	± 30	V
I_C	Collector Current	30	A
	Collector Current @ $T_C = 100^{\circ}\text{C}$	15	A
I_{Cpuls}	Pulsed Collector Current, t_p limited by T_{jmax}	45	A
-	turn off safe operating area, $V_{CE}=1200\text{V}$, $T_j=175^{\circ}\text{C}$	45	A
I_F	Diode Continuous Forward Current @ $T_C = 100^{\circ}\text{C}$	15	A
I_{FM}	Diode Maximum Forward Current	45	A
P_D	Power Dissipation @ $T_C = 25^{\circ}\text{C}$	300	W
	Power Dissipation @ $T_C = 100^{\circ}\text{C}$	150	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +175	$^{\circ}\text{C}$
T_L	Maximum Temperature for Soldering	260	$^{\circ}\text{C}$
t_{sc}	Short circuit withstand time $V_{GE}=15.0\text{V}$, $V_{CC} \leq 600\text{V}$, Allowed number of short circuits<1000Time between short circuits: $\geq 1.0\text{s}, T_j \leq 150^{\circ}\text{C}$	10	us

Thermal Characteristic

Symbol	Parameter	Value	Units
R _{θJC}	Thermal Resistance, Junction to case for IGBT	0.50	°C/W
R _{θJC}	Thermal Resistance, Junction to case for Diode	0.93	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	40	°C/W

Electrical Characteristics (T_c=25°C unless otherwise noted)

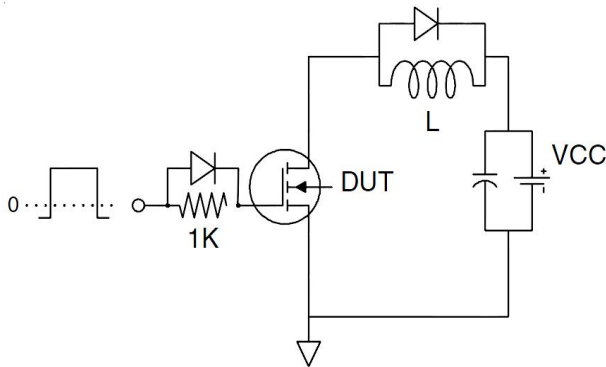
Symbol	Parameter	Conditions	Value			Units	
			Min.	Typ.	Max.		
Static Characteristics							
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0V, I _{CE} =1mA	1200	--	--	V	
I _{CES}	Collector-Emitter Leakage Current	V _{GE} =0V, V _{CE} =1200V	--	--	5	μA	
I _{GES(F)}	Gate to Emitter Forward Leakage	V _{GE} =+30V, V _{CE} =0V	--	--	200	nA	
I _{GES(R)}	Gate to Emitter Reverse Leakage	V _{GE} =-30V, V _{CE} =0V	--	--	200	nA	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	V _{GE} =15V, I _C =15A	T _J =25°C	--	1.55	1.80	V
			T _J =175°C	--	1.80	--	V
V _{GE(th)}	Gate Threshold Voltage	I _C =1mA, V _{CE} =V _{GE}	5.0	--	6.5	V	
I _{C(SC)}	Short circuit collector current Max.1000 short circuits Time between short circuits: ≥1.0s	V _{GE} =15V, V _{CC} ≤600V, t _{SC} ≤10μs, T _J ≤150°C	--	80	--	A	
Dynamic Characteristics							
C _{ies}	Input Capacitance	V _{CE} =30V, V _{GE} =0V, f=1MHz	--	1430	--	pF	
C _{oes}	Output Capacitance		--	35	--		
C _{res}	Reverse Transfer Capacitance		--	25	--		
Q _g	Total Gate Charge	V _{CC} =600V, I _C =15A V _{GE} =15V	--	90	--	nC	
Q _{ge}	Gate to Emitter Charge		--	11	--	nC	
Q _{gc}	Gate to Collector Charge		--	58	--	nC	
Switching Characteristics							
t _{d(ON)}	Turn-on Delay Time	V _{CE} =600V, I _C =15A V _{GE} =0/15V, R _g =8Ω Inductive Load	--	19	--	ns	
t _r	Rise Time		--	17	--		
t _{d(OFF)}	Turn-Off Delay Time		--	170	--		
t _f	Fall Time		--	18	--		
E _{on}	Turn-On Switching Loss		--	0.9	--	mJ	
E _{off}	Turn-Off Switching Loss		--	0.6	--		
E _{ts}	Total Switching Loss		--	1.5	--		

Electrical Characteristics of the Diode (T_c= 25°C unless otherwise specified)

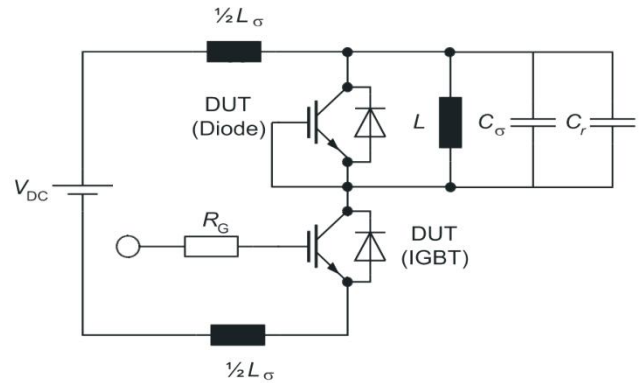
Symbol	Parameter	Conditions	Rating			Units
			Min.	Typ.	Max.	
V _{FM}	Diode Forward Voltage	I _F =15A	--	2.2	2.8	V
T _{rr}	Reverse Recovery Time	I _F =15A, di/dt=200A/μs	--	120	--	ns
I _{RRM}	Diode Peak Reverse Recovery Current		--	12	--	A
Q _{rr}	Reverse Recovery Charge		--	0.72	--	μC
Pulse width t _p ≤380μs, δ≤2%						

Test Circuit

1) Gate Charge Test Circuit

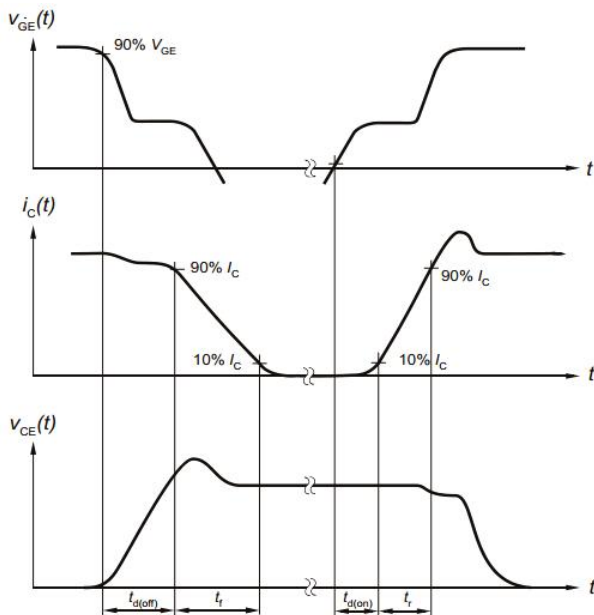


2) Switch Time Test Circuit

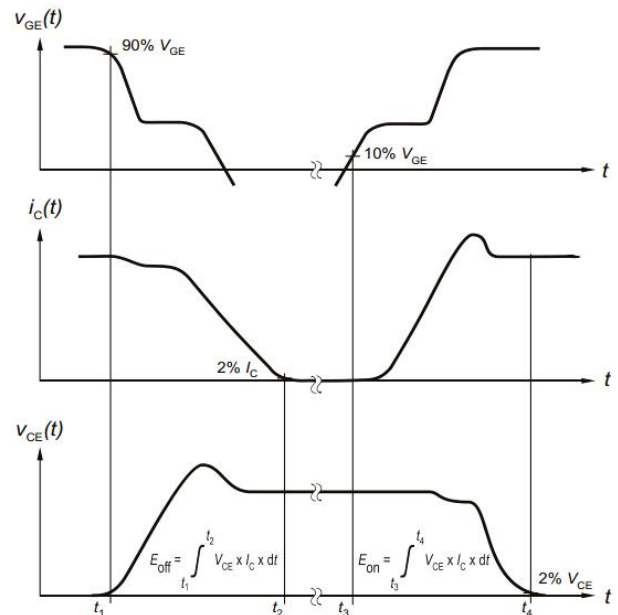


Switching characteristics

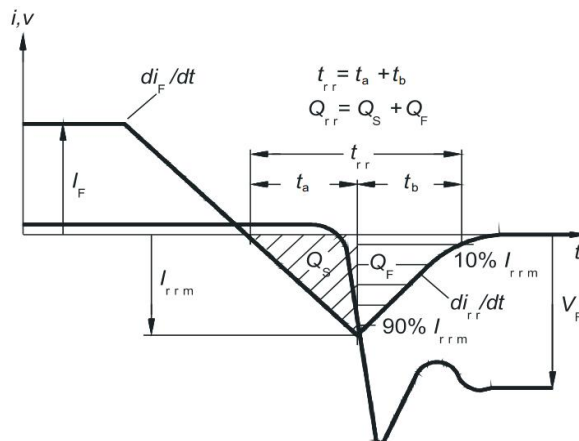
1) Definition of switching times



2) Definition of switching losses



3) Definition of diode switching characteristics



Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

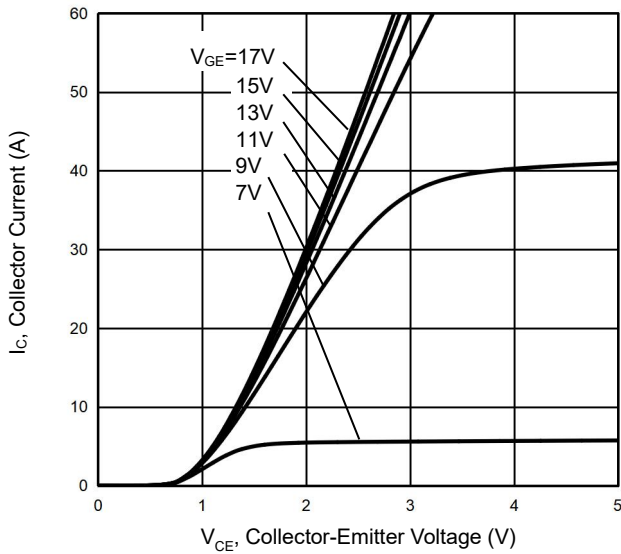


Figure 2 Transfer Characteristics

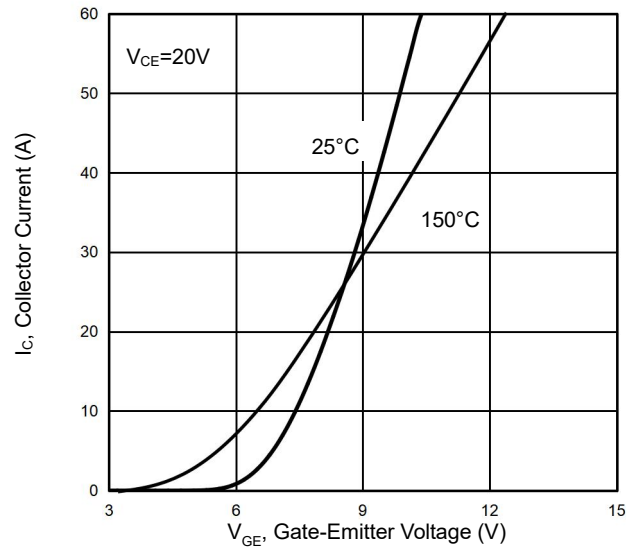


Figure 3 $V_{CE(sat)}$ vs. Case Temperature

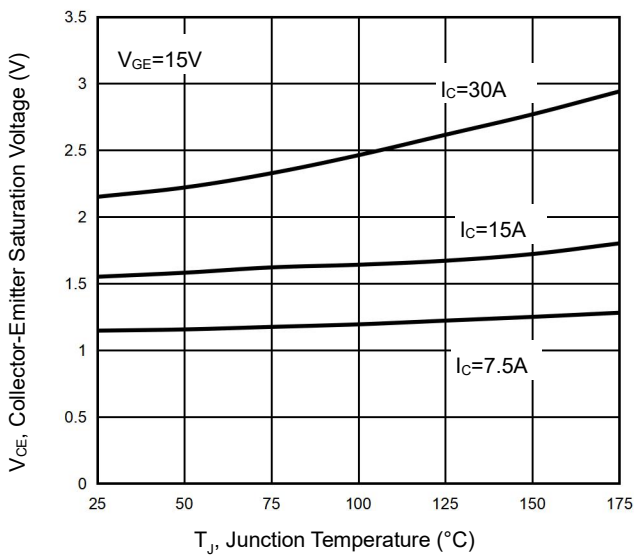


Figure 4 Saturation Voltage vs. V_{GE}

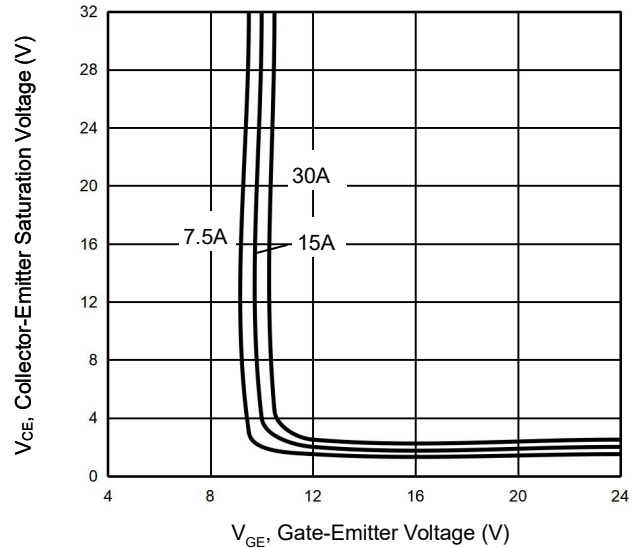


Figure 5 Capacitance Characteristics

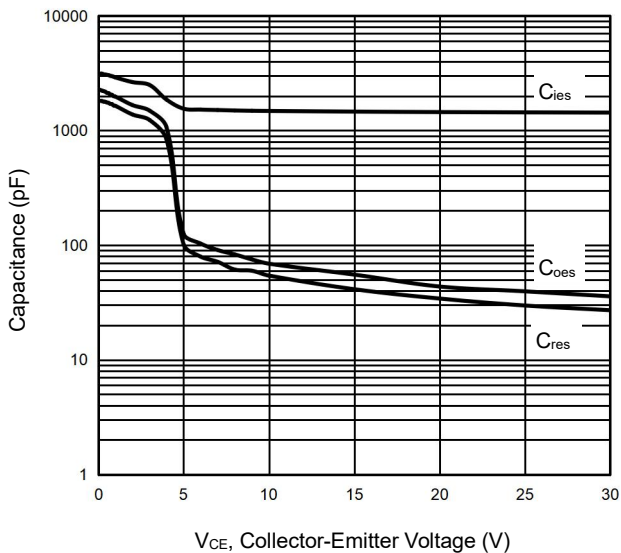
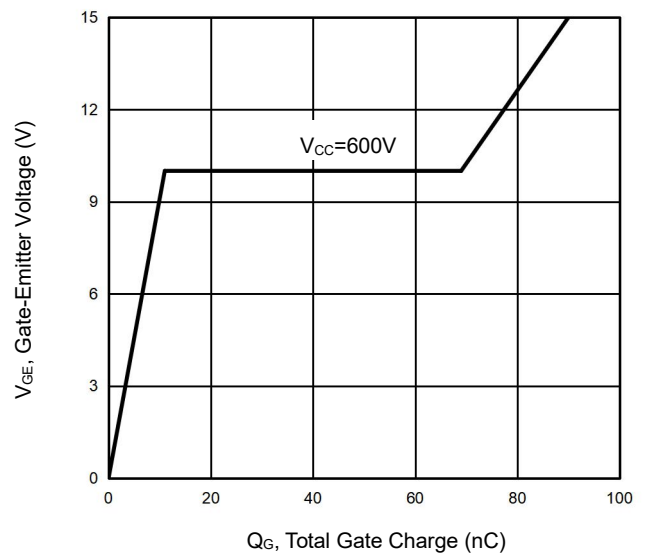


Figure 6 Gate Charge Wave Form



Typical Electrical and Thermal Characteristics

Figure 7 Forward Characteristics

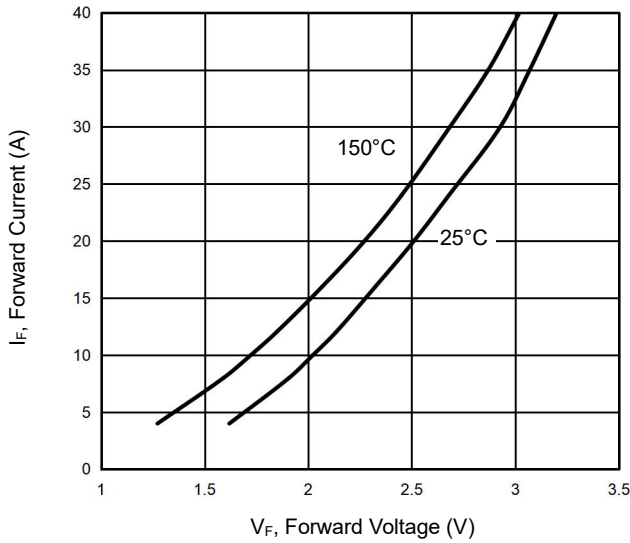


Figure 8 V_F vs. Temperature

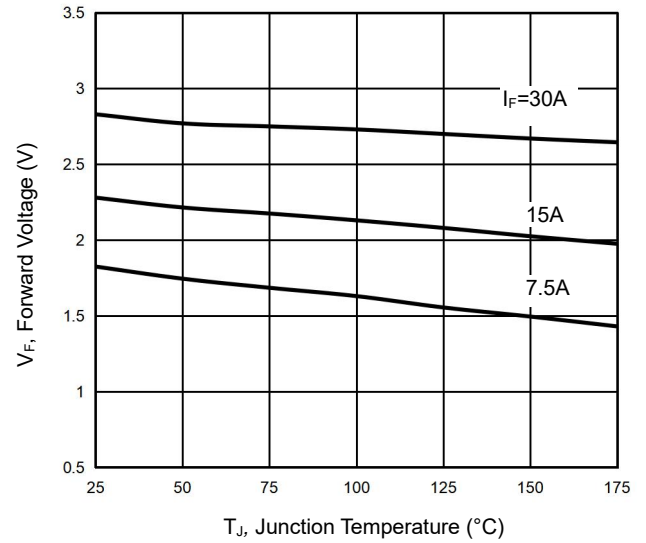


Figure 9 Switching Energy vs. Temperature

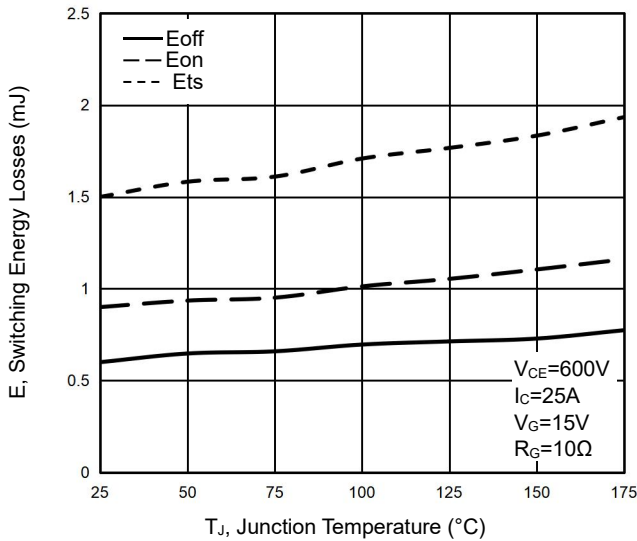


Figure 10 P_{tot} vs. Case Temperature

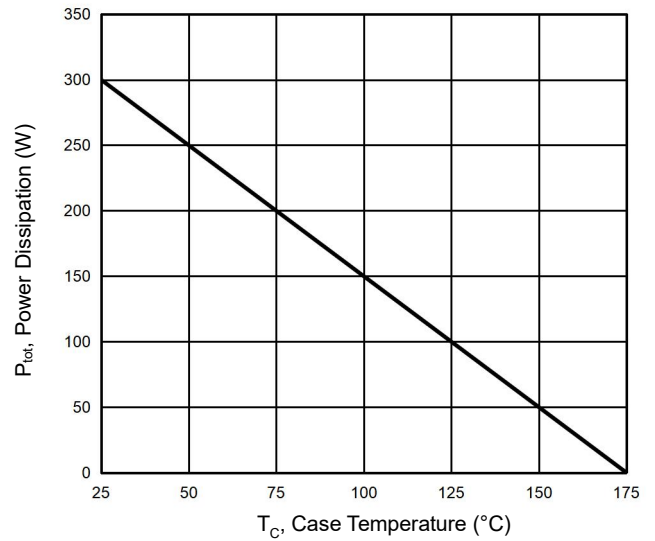


Figure 11 Gate-Emitter Threshold Voltage as a Function of Junction Temperature

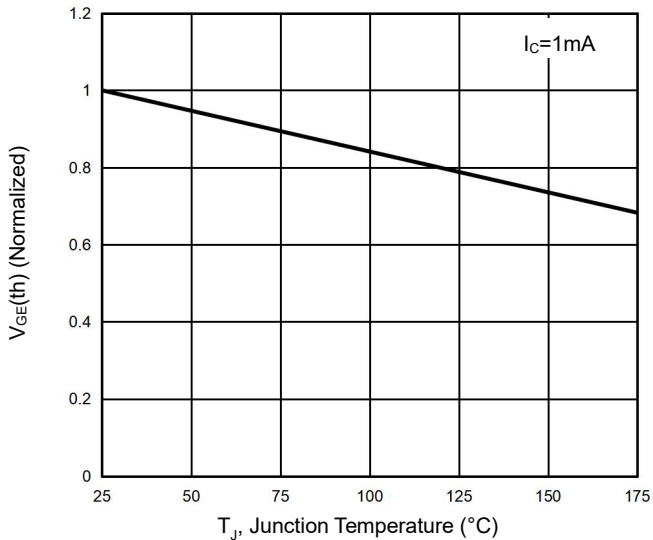
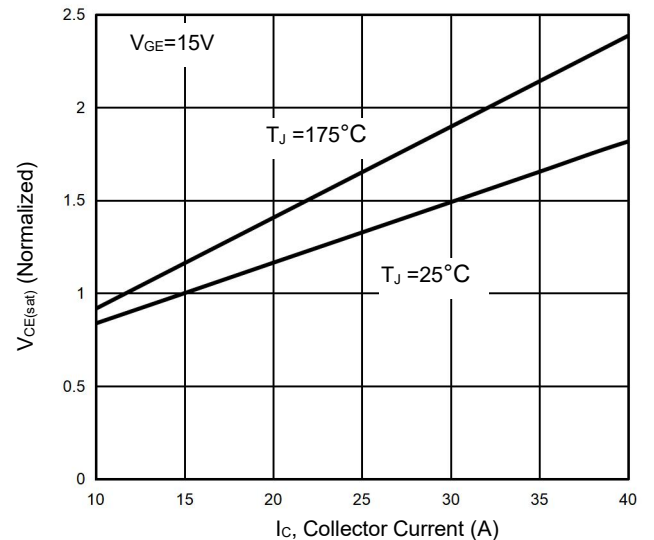


Figure 12 Typical Collector-Emitter Saturation Voltage as a function of Collector Current



Typical Electrical and Thermal Characteristics

Figure 13 IGBT Transient Thermal Impedance

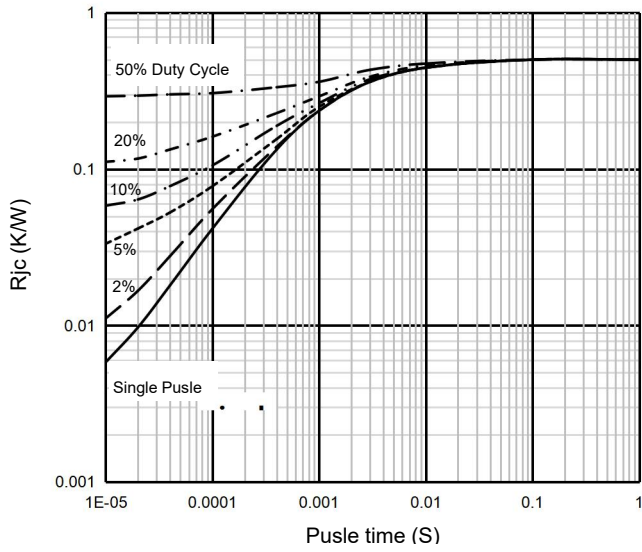
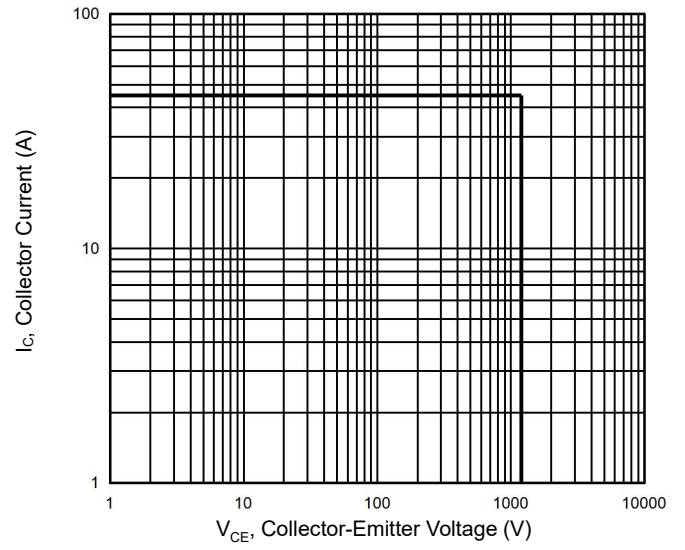
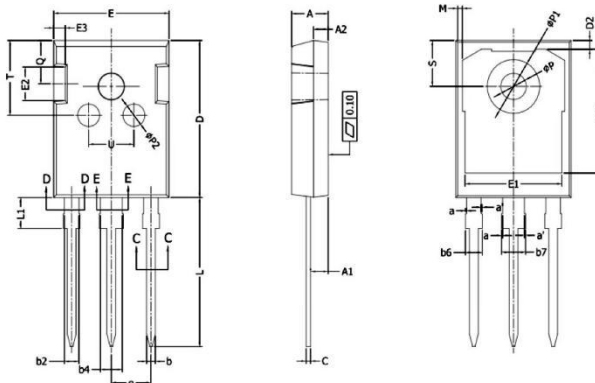


Figure 14 Reverse Bias SOA

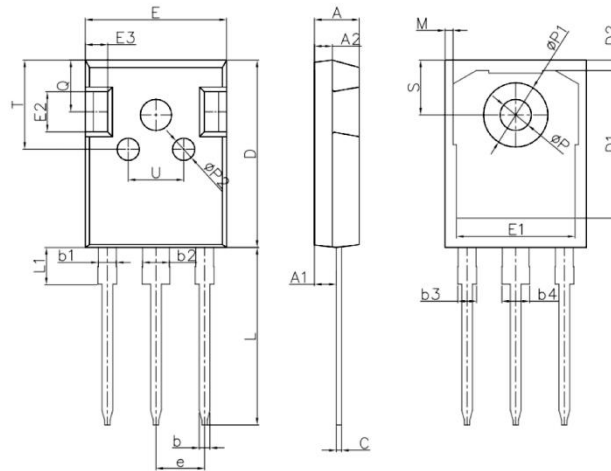


TO-247-P Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.90	5.10	0.19	0.20
A1	2.31	2.51	0.09	0.10
A2	1.90	2.10	0.08	0.09
a	0.00	0.15	0.00	0.01
a'	0.00	0.15	0.00	0.01
b	1.16	1.26	0.05	0.06
b2	1.96	2.06	0.08	0.09
b4	2.96	3.06	0.12	0.13
b6	-	2.25	-	0.09
b7	-	3.25	-	0.13
C	0.59	0.66	0.02	0.03
D	20.90	21.10	0.82	0.83
D1	16.25	16.85	0.64	0.66
D2	1.05	1.35	0.04	0.05
E	15.70	15.90	0.62	0.63
E1	13.10	13.50	0.52	0.53
E2	4.40	4.60	0.17	0.18
E3	2.40	2.60	0.09	0.10
e	5.436 BSC		0.214 BSC	
L	19.80	20.10	0.78	0.79
L1	-	4.30	-	0.17
M	0.35	0.95	0.01	0.04
P	3.40	3.60	0.13	0.14
P1	7.00	7.40	0.28	0.29
P2	2.40	2.60	0.09	0.10
Q	5.60	6.00	0.22	0.24
S	6.05	6.25	0.24	0.25
T	9.80	10.20	0.39	0.40
U	6.00	6.40	0.24	0.25

TO-247-E Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.90	5.10	0.19	0.20
A1	2.31	2.51	0.09	0.10
A2	1.90	2.10	0.07	0.08
b	1.16	1.26	0.05	0.06
b1	1.96	2.06	0.08	0.09
b2	2.96	3.06	0.12	0.13
b3	--	2.25	--	0.09
b4	--	3.25	--	0.13
c	0.59	0.66	0.02	0.03
D	20.90	21.10	0.82	0.83
D1	16.25	16.85	0.64	0.66
D2	1.05	1.35	0.04	0.05
E	15.70	15.90	0.62	0.63
E1	13.10	13.50	0.52	0.53
E2	4.40	4.60	0.17	0.18
E3	2.40	2.60	0.09	0.10
e	5.436 BSC		0.214 BSC	
L	19.80	20.10	0.78	0.79
L1	--	4.30	--	0.17
M	0.35	0.95	0.01	0.04
P	3.40	3.60	0.13	0.14
P1	7.00	7.40	0.28	0.29
P2	2.40	2.60	0.09	0.10
Q	5.60	6.00	0.22	0.24
S	6.05	6.25	0.24	0.25
T	9.80	10.20	0.39	0.40
U	6.00	6.40	0.24	0.25

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